

2N396 Datasheet, Equivalent, Cross Reference Search

Type Designator: 2N396

Material of Transistor: Ge

Polarity: PNP

Maximum Collector Power Dissipation (P_c): 0.15 W

Maximum Collector-Base Voltage $|V_{cb}|$: 30 V

Maximum Emitter-Base Voltage $|V_{eb}|$: 20 V

Maximum Collector Current $|I_c \text{ max}|$: 0.2 A

Max. Operating Junction Temperature (T_j): 100 °C

Transition Frequency (f_t): 4 MHz

Collector Capacitance (C_c): 24 pF

Forward Current Transfer Ratio (h_{FE}), MIN: 30

Noise Figure, dB: -

Package: TO5